L Number	Hits	Search Text	DB	Time stamp
4	2512	· · · · · · · · · · · · · · · · · · ·	USPAT;	2003/09/21 20:17
		deposition) ald (sequential digital) adj	US-PGPUB	
		(CVD chemical adj vapor adj deposition)))		
б	12	, , , ,	USPAT;	2003/09/21 20:17
		deposition) ald (sequential digital) adj	US-PGPUB	
		(CVD chemical adj vapor adj deposition)))		
5	38) and nanolaminate) and silicide (((atomic adj layer adj (epitaxy	IICDAT.	2003/09/21 20:42
5	30	(((atomic ad) layer ad) (epitaxy deposition) ald (sequential digital) adj	USPAT; US-PGPUB	2003/09/21 20:42
		(CVD chemical adj vapor adj deposition)))	05-16100	İ
) and nanolaminate		
7	1		USPAT;	2003/09/21 20:39
		•	US-PGPUB	
8	1	("6287635").PN.	USPAT;	2003/09/21 20:36
			US-PGPUB	
9	0	nanolaminate with WSi\$	USPAT;	2003/09/21 20:40
1.0			US-PGPUB	
10	1	nanolaminate same (WSi\$ silicide)	USPAT;	2003/09/21 20:37
11	1	09/954705.app.	US-PGPUB	2002/00/21 20-20
T T	1	09/954/05.app.	USPAT; US-PGPUB	2003/09/21 20:39
12	65	nanolaminate	USPAT;	2003/09/21 20:40
		Trans-tantina ed	US-PGPUB	2003/03/21 20.40
_	3606	(427/250-253,255.18,255.17,255.23,255.26,25		28803809288 B9343CCLS
		(== , == = , == = , = , = = , = = , = = , = = , = = , = = , = = , = = , = = , = = , = , = = , = = , = = , = = , = , = = , = , = = , = = , = , = = , =	US-PGPUB	
_	146	((427/250-253,255.18,255.17,255.23,255.26,2		,2853392/28513937.CCLS.
		and tungsten with silicide	US-PGPUB	
-	3	' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '	255PAT;255.3	12065/09220557393).CCLS
		and tungsten with silicide) and (atomic	US-PGPUB	
_) 4	4dj42av250a253d255s18j255c17A2D5.23,255.26,		12065/09220557392).CCLS
	1067	and tungsten with silicide) and (atomic	US-PGPUB	
_	4867	4427/248r1a250d250s255on8o25ALDY,255.23,255		158003/09\$28927238.393).
_	57	((427/248.1,250-253,255.18,255.17,255.23,25	US-PGPUB	202100400200-005
	37	and (atomic adj layer adj deposition or	US-PGPUB	22003192220322; 223.393)
_	5	ALD#27/248.1,250-253,255.18,255.17,255.23,2		2883309288 3820255 393
		and (atomic adj layer adj deposition or	US-PGPUB	,20000011,200.1102,0200.000
_	0	ADD052896.appgsten with silicide	USPAT;	2003/09/20 17:14
			US-PGPUB	
_	1705	atomic adj layer adj deposition or ALD	USPAT;	2003/09/20 17:17
			US-PGPUB	
_	90	(atomic adj layer adj deposition or ALD)	USPAT;	2003/09/20 17:35
	89	and tungsten with silicide (atomic adj layer adj deposition or ALD)	US-PGPUB	2003/09/20 18:02
	09	and WSi\$7	USPAT; US-PGPUB	2003/09/20 18:02
_	58	((atomic adj layer adj deposition or ALD)	USPAT;	2003/09/20 17:36
		and WSi\$7) not ((atomic adj layer adj	US-PGPUB	2003/03/20 17:30
		deposition or ALD) and tungsten with		
		silicide)		
-	0	(((a real of the second of	USPAT;	2003/09/20 17:36
		and WSi\$7) not ((atomic adj layer adj	US-PGPUB	
		deposition or ALD) and tungsten with		
_	1 1	silicide)) and @ad<=2001020	TIOD 3 TO	0002/00/02 12 15
	14	(((atomic adj layer adj deposition or ALD) and WSi\$7) not ((atomic adj layer adj	USPAT;	2003/09/20 19:15
		deposition or ALD) and tungsten with	US-PGPUB	
		silicide)) and @ad<=20001020		
-	71		USPAT;	2003/09/20 17:43
	_		US-PGPUB	1000,00,20 1,.30
- ,	5	((427/255.392).CCLS.) and (atomic adj	USPAT;	2003/09/20 19:12
		layer adj deposition ald (sequential	US-PGPUB	
		digital) adj (CVD chemical adj vapor adj		
		deposition))		
-	2	((427/255.392).CCLS.) and (atomic adj	USPAT;	2003/09/20 18:01
_	58	layer adj epitaxy ale)	US-PGPUB	200242040040200
	38	((427/248.1,250-253,255.18,255.17,255.23,25 and (atomic adj layer adj epitaxy or ALE)		220U3LYX\$\$U3YX;0\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\
_	0	(((427/248.1,250-253,255.18,255.17,255.23,2	US-PGPUB	2883300388 302025 202
		and (atomic adj layer adj epitaxy or ALE))	US-PGPUB	, 2003pwpk20. 1029233.393
	L	and WSi\$7	100 10100	

	1	(((427/248.1,250-253,255.18,255.17,255.23,2		,2663309286.8829255.393)
_	2512	and (atomic adj layer adj epitaxy or ALE)) andomingadenlwyth adlicedtaxy deposition)	US-PGPUB .	2002/00/20 20-11
-	2512	ald (sequential digital) adj (CVD chemical	USPAT; US-PGPUB	2003/09/20 20:11
		adj vapor adj deposition))	US-FGFUB	
_	0	((atomic adj layer adj (epitaxy	USPAT;	2003/09/21 20:16
		deposition) ald (sequential digital) adj	US-PGPUB	2000/05/21 20:10
		(CVD chemical adj vapor adj deposition)))		
		and hydrate with substrate		
-	1	((atomic adj layer adj (epitaxy	USPAT;	2003/09/20 19:15
		deposition) ald (sequential digital) adj	US-PGPUB	İ
		(CVD chemical adj vapor adj deposition))) and hydrated with substrate		
_	130		USPAT;	2003/09/20 20:50
	100	deposition) ald (sequential digital) adj	US-PGPUB	2003/03/20 20:30
		(CVD chemical adj vapor adj deposition)))	00 10105	
		and atomic with hydrogen		
-	22	1 (1 (1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 -	USPAT;	2003/09/20 19:43
1		deposition) ald (sequential digital) adj	US-PGPUB	
İ		(CVD chemical adj vapor adj deposition)))		
		and atomic with hydrogen) and @ad<=20001020) and (silicide tungsten		
		titanium)	Ì	
_	65	'	USPAT;	2003/09/20 19:42
		deposition) ald (sequential digital) adj	US-PGPUB	
		(CVD chemical adj vapor adj deposition)))		
	10	and atomic adj hydrogen		
-	49	(((atomic adj layer adj (epitaxy deposition) ald (sequential digital) adj	USPAT;	2003/09/20 19:43
		(CVD chemical adj vapor adj deposition)))	US-PGPUB	
		and atomic adj hydrogen) and (silicide		
1		tungsten titanium)		
-	14	((((atomic adj layer adj (epitaxy	USPAT;	2003/09/20 19:50
		deposition) ald (sequential digital) adj	US-PGPUB	
		(CVD chemical adj vapor adj deposition)))		
		and atomic adj hydrogen) and (silicide tungsten titanium)) and @ad<=20001020		
_	1209		USPAT;	2003/09/20 19:50
		chloride halogen halide)	US-PGPUB	2003/03/20 13:30
-	3	(hydrogen with reduce with (chlorine	USPAT;	2003/09/20 20:00
		chloride halogen halide)) and (atomic adj	US-PGPUB	
		layer adj (epitaxy deposition) ald		
		(sequential digital) adj (CVD chemical adj vapor adj deposition))		
_	100		USPAT;	2003/09/20 20:01
			US-PGPUB	2003/03/20 20:01
-	85	(hydrogen with scavenge with chlori?e) and	USPAT;	2003/09/20 20:01
		@ad<=20001020	US-PGPUB	
-	3	((hydrogen with scavenge with chlori?e)	USPAT;	2003/09/20 20:03
_	4	and @ad<=20001020) and silicide ((hydrogen with scavenge with chlori?e)	US-PGPUB USPAT;	2002/00/20 20-04
	-	and @ad<=20001020) and tungsten	USPAT; US-PGPUB	2003/09/20 20:04
-	2	((hydrogen with scavenge with chlori?e)	USPAT;	2003/09/20 20:05
		and @ad<=20001020) and (CVD ALD atomic adj	US-PGPUB	
	Į	layer adj (deposition epitaxy) chemical		
_	48	adj vapor adj deposition)	110000	2002/02/02/02
-	40	((atomic adj layer adj (epitaxy deposition) ald (sequential digital) adj	USPAT;	2003/09/20 20:12
		(CVD chemical adj vapor adj deposition)))	US-PGPUB	
	1	and tungsten adj layer		
_	25	(((atomic adj layer adj (epitaxy	USPAT;	2003/09/20 20:12
1		deposition) ald (sequential digital) adj	US-PGPUB	
		(CVD chemical adj vapor adj deposition)))		
_	45	and tungsten adj layer) and hydrogen (((atomic adj layer adj (epitaxy	IICDAM -	3003/00/30 00 50
	1 1	deposition) ald (sequential digital) adj	USPAT; US-PGPUB	2003/09/20 20:50
1		(CVD chemical adj vapor adj deposition)))	22 10100	
		and atomic with hydrogen) and		
		@ad<=20001020		

-	65	((atomic adj layer adj (epitaxy	USPAT;	2003/09/20 20:50
		deposition) ald (sequential digital) adj	US-PGPUB	
		(CVD chemical adj vapor adj deposition)))		
		and atomic adj hydrogen	{	{